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Journal Information

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Classification History

Year	A+	A	B	C
2026		✓	✓	
2025		✓	✓	
2024		✓	✓	
2023		✓	✓	
2021/2022		✓	✓	
2020		✓	✓	
2019		✓	✓	
2018		✓		

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DOI: 10.1016/j.sse.2026.109432

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2027-1 Vol. 239 Pages 109419
Authors: Yixian Song, Xiaoyun Huang, Yan Pan et al.
DOI: 10.1016/j.sse.2026.109419

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Authors: Ruhiddin Yuldoshov, Abdurashid Mavlanov, Kudrat Kuchkarov et al.
DOI: 10.1016/j.sse.2026.109418

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DOI: 10.1016/j.sse.2026.109422

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Authors: Abderrahmane Zakarya Djennati, Mohammed Khaouani, Mohammed Anes Belbachir et al.
DOI: 10.1016/j.sse.2026.109437